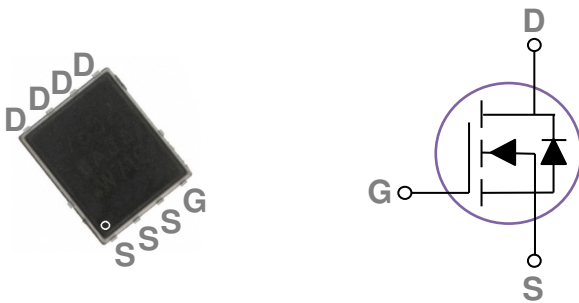


General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
30V	7.8mΩ	60A

PPAK5x6 Pin Configuration



Features

- 30V,60A, $R_{DS(ON)} = 7.8m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C=25^\circ C$)	60	A
	Drain Current – Continuous ($T_C=100^\circ C$)	38	A
I_{DM}	Drain Current – Pulsed ¹	240	A
EAS	Single Pulse Avalanche Energy ²	45	mJ
IAS	Single Pulse Avalanche Current ²	30	A
P_D	Power Dissipation ($T_C=25^\circ C$)	54	W
	Power Dissipation – Derate above $25^\circ C$	0.43	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.3	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Static State Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.04	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =24V, V _{GS} =0V, T _J =125°C	---	---	10	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =16A	---	6.5	7.8	mΩ
		V _{GS} =4.5V, I _D =8A	---	9.2	12	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	1.2	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =8A	---	9.5	---	S

Dynamic Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =15V, V _{GS} =4.5V, I _D =20A	---	7.5	12	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	4.5	8	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	1.3	2.6	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =15A	---	4.8	9	ns
T _r	Rise Time ^{3, 4}		---	12.5	24	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	27.6	52	
T _f	Fall Time ^{3, 4}		---	8.2	16	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	680	1000	pF
C _{oss}	Output Capacitance		---	150	220	
C _{rss}	Reverse Transfer Capacitance		---	70	105	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	2.7	5.4	Ω

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V _{DD} =25V, L=0.1mH, I _{AS} =15A	12	---	---	mJ

Drain-Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	60	A
I _{SM}	Pulsed Source Current ³		---	---	240	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =10A, di/dt=100A/μs	---	8.1	---	ns
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	1.6	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=30A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

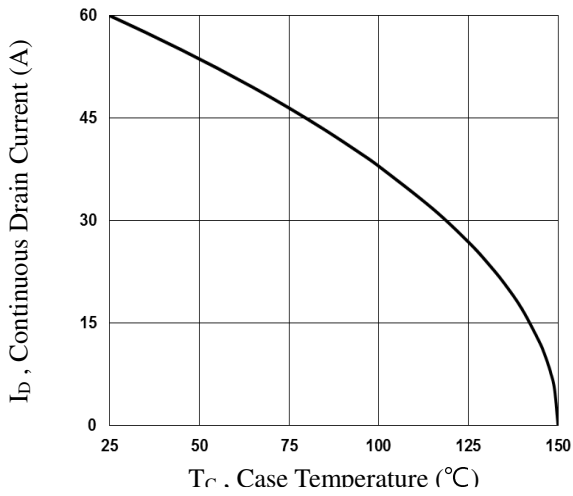


Fig.1 Continuous Drain Current vs. T_c

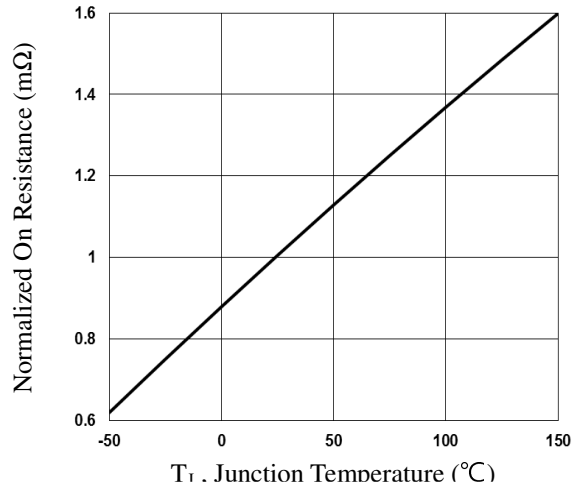


Fig.2 Normalized R_{DSon} vs. T_j

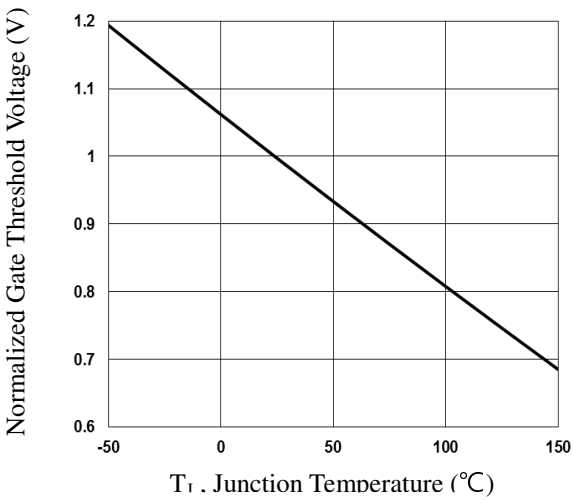


Fig.3 Normalized V_{th} vs. T_j

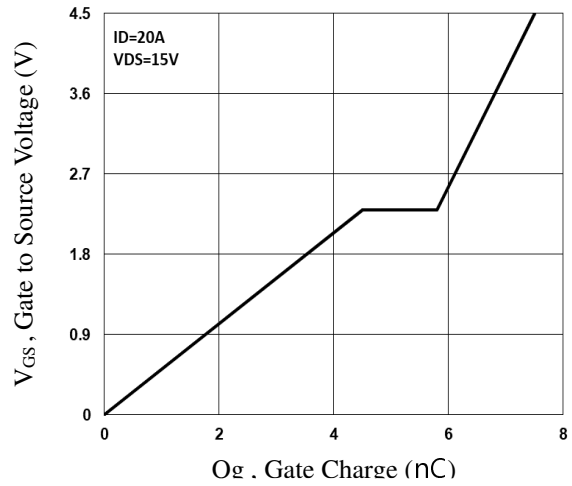


Fig.4 Gate Charge Waveform

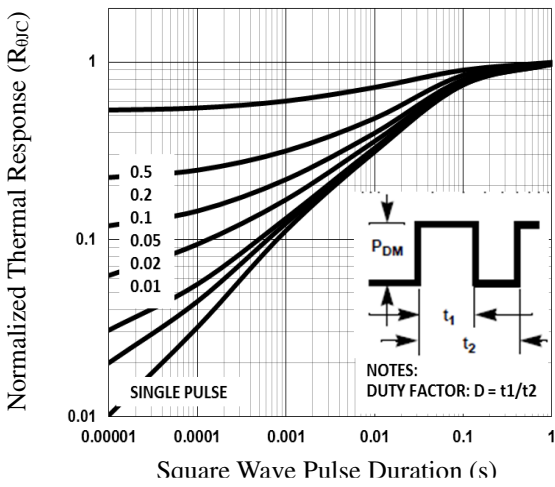


Fig.5 Normalized Transient Impedance

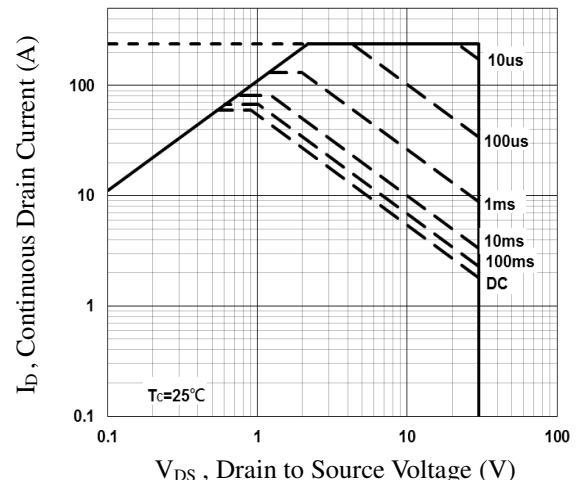


Fig.6 Maximum Safe Operation Area

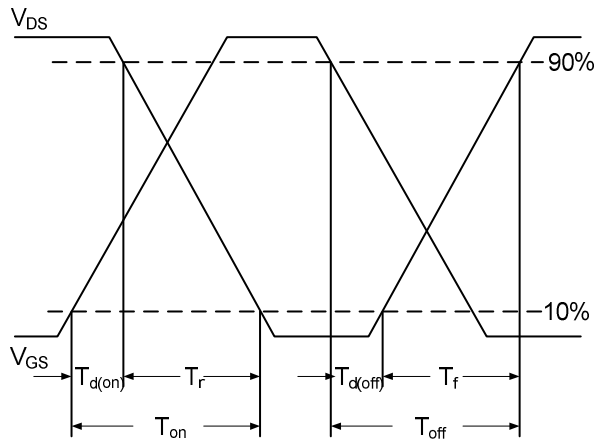


Fig.7 Switching Time Waveform

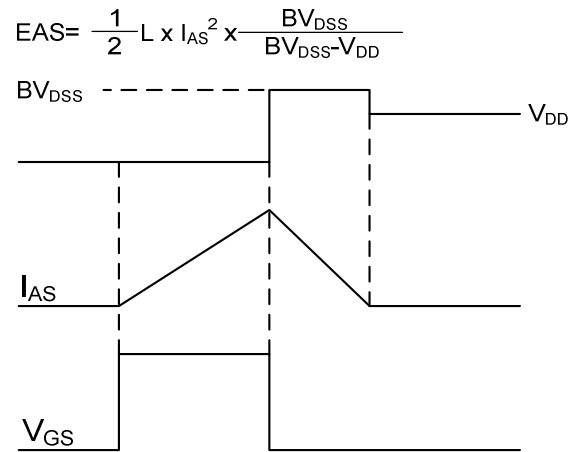
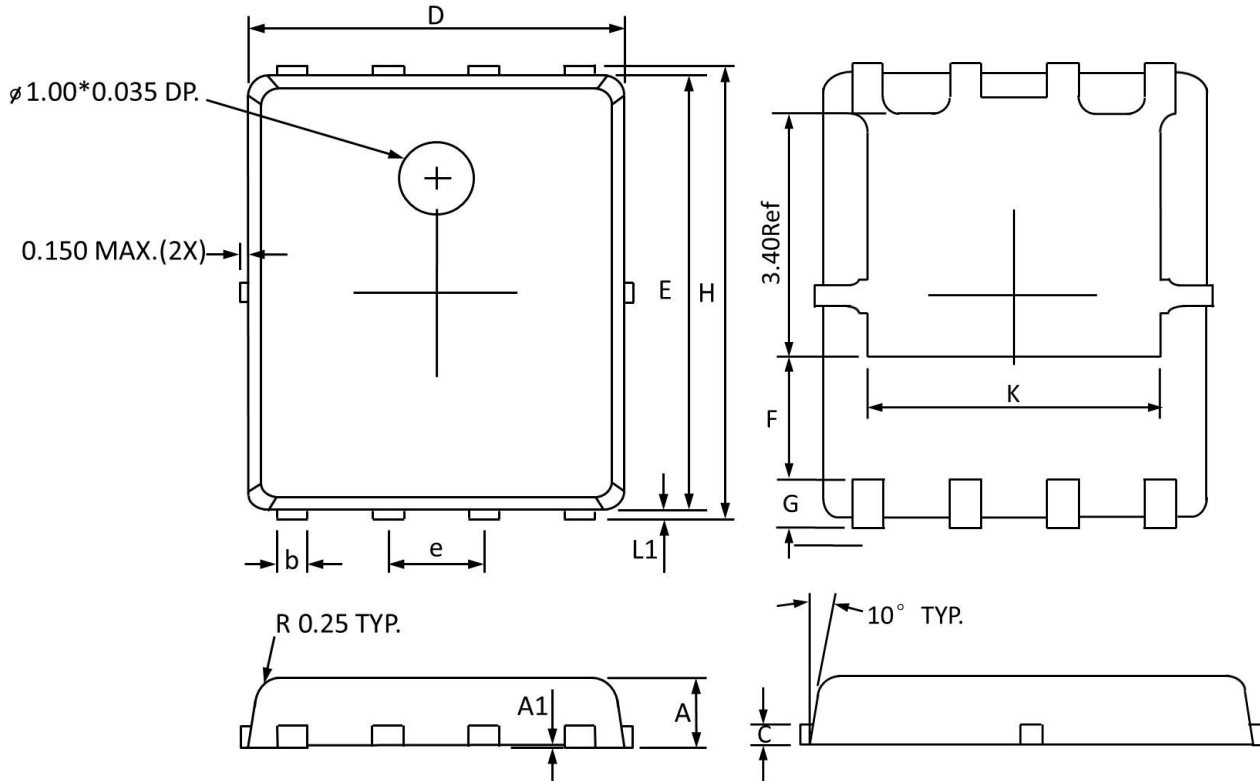


Fig.8 EAS Waveform

PPAK5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.000	0.032	0.039
A1	0.000	0.005	0.000	0.000
b	0.350	0.490	0.014	0.019
C	0.254 Ref		0.254 Ref	
D	4.900	5.100	0.193	0.200
E	5.700	5.900	0.225	0.232
e	1.27 BSC		1.27 BSC	
F	1.400 Ref		1.400 Ref	
G	0.600 Ref		0.600 Ref	
H	5.950	6.200	0.235	0.244
L1	0.100	0.180	0.004	0.007
K	4.000 Ref		4.000 Ref	